

FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

Ratings	Symbol	2N3878	Unit
Collector-Emitter Voltage	V_{CE0}	50	Vdc
Collector-Base Voltage	V_{CBO}	120	Vdc
Emitter-Base Voltage	V_{EBO}	7.0	Vdc
Collector Current	I_C	4.0	Adc
Total Power Dissipation $T_C = 25^\circ\text{C}$	P_D	35	W
Operating & Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case	$R_{\theta JC}$	5.0	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage $I_C = 200\text{mA}, I_B = 0$	$V_{CE0(sus)}$	50	-	V
Emitter-Base Cutoff Current $V_{EB} = 7.0\text{Vdc}, I_C = 0$	I_{EBO}	-	10	mAdc
Collector-Emitter Saturation Voltage $I_C = 4.0\text{Adc}, I_B = 0.4\text{Adc}$	$V_{CE(sat)}$	-	2.0	Vdc
Base-Emitter On Voltage $I_C = 4\text{Adc}, V_{CE} = 2\text{Vdc}$	$V_{BE(on)}$	-	2.5	V
Forward Current Transfer Ratio $I_C = 0.5\text{Adc}, V_{CE} = 2.0\text{Vdc}$ $I_C = 4.0\text{Adc}, V_{CE} = 2.0\text{Vdc}$ $I_C = 4.0\text{Adc}, V_{CE} = 5.0\text{Vdc}$ $I_C = 0.5\text{Adc}, V_{CE} = 5.0\text{Vdc}$	h_{FE}	40 8 20 50	200 - - 200	-

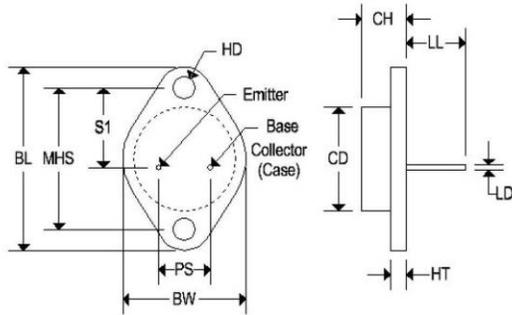
Note 1: Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$

2N3878

NPN SILICON POWER TRANSISTOR

MECHANICAL CHARACTERISTICS

Case	TO-66
Marking	Alpha-numeric
Polarity	See below



Dim	TO-66			
	Inches		Millimeters	
	Min	Max	Min	Max
BL	1.205	1.280	30.60	32.50
CD	0.445	0.557	11.303	14.148
CH	0.257	0.284	6.540	7.220
LL	0.374	0.413	9.500	10.50
BW	0.680	0.727	17.26	18.46
LD	0.030	0.036	0.760	0.920
HT	0.054	0.065	1.380	1.650
MHS	0.951	0.976	24.16	24.78
S1	0.545	0.614	13.84	15.60
HD	0.131	0.154	3.320	3.920
PS	0.191	0.210	4.860	5.340